



SANYO Semiconductors

## DATA SHEET

# 2SC6118LS

 — NPN Triple Diffused Planar Silicon Transistor  
**Color TV Horizontal Deflection Output Applications**

## Features

- High speed.
- High breakdown voltage ( $V_{CB0}=1500V$ ).
- High reliability (Adoption of HVP process).
- Adoption of MBIT process.
- On-chip damper diode.

## Specifications

**Absolute Maximum Ratings** at  $T_a=25^\circ C$ 

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	$V_{CB0}$		1500	V
Collector-to-Emitter Voltage	$V_{CEO}$		800	V
Emitter-to-Base Voltage	$V_{EBO}$		6	V
Collector Current	$I_C$		8	A
Collector Current (Pulse)	$I_{CP}$		20	A
Collector Dissipation	$P_C$		2.0	W
		$T_c=25^\circ C$	35	W
Junction Temperature	$T_J$		150	$^\circ C$
Storage Temperature	$T_{stg}$		-55 to +150	$^\circ C$

**Electrical Characteristics** at  $T_a=25^\circ C$ 

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=800V, I_E=0A$			10	$\mu A$
Collector Cutoff Current	$I_{CES}$	$V_{CE}=1500V, R_{BE}=0\Omega$			1.0	mA
Collector Sustain Voltage	$V_{CEO(sus)}$	$I_C=100mA, I_B=0A$	800			V
Emitter Cutoff Current	$I_{EBO}$	$V_{EB}=4V, I_C=0A$	40		130	mA

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**SANYO Semiconductor Co., Ltd.**

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# 2SC6118LS

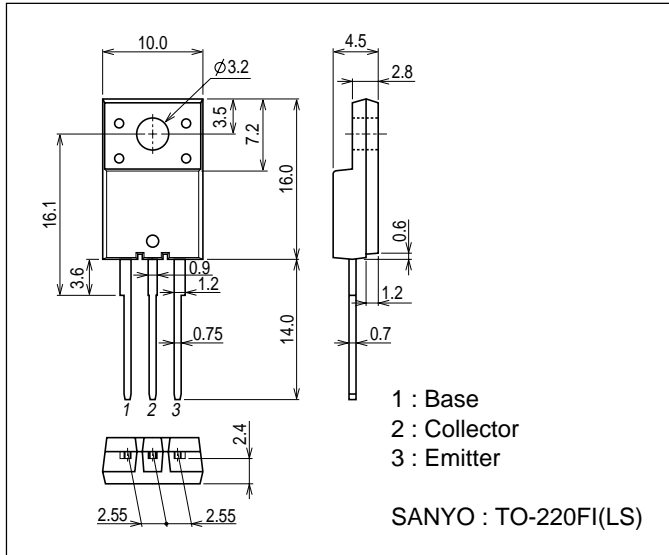
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=4.5A, I_B=0.9A$			2	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=4.5A, I_B=0.9A$			1.5	V
DC Current Gain	$h_{FE1}$	$V_{CE}=5V, I_C=1A$	10			
	$h_{FE2}$	$V_{CE}=5V, I_C=5A$	5.3		7.5	
Diode Forward Voltage	$V_F$	$I_{EC}=7A$			2	V
Fall Time	$t_f$	$I_C=3A, I_{B1}=0.6A, I_{B2}=-1.2A$			0.2	$\mu s$

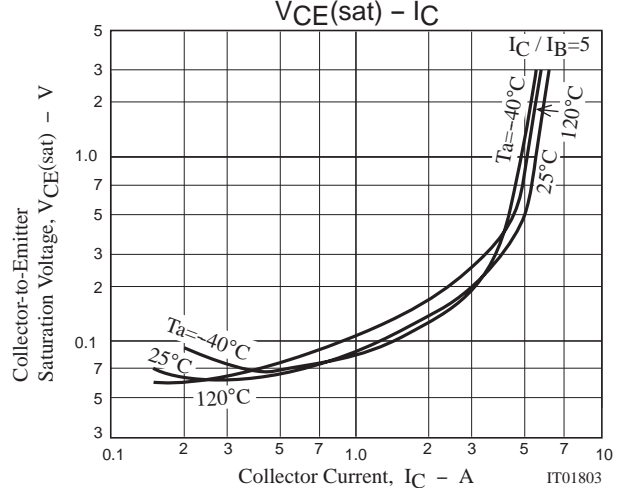
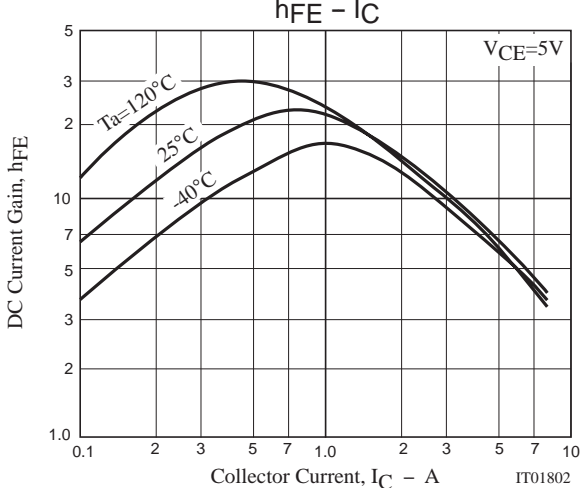
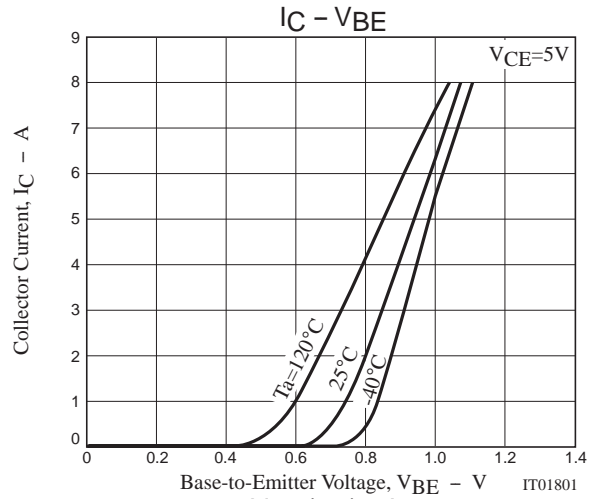
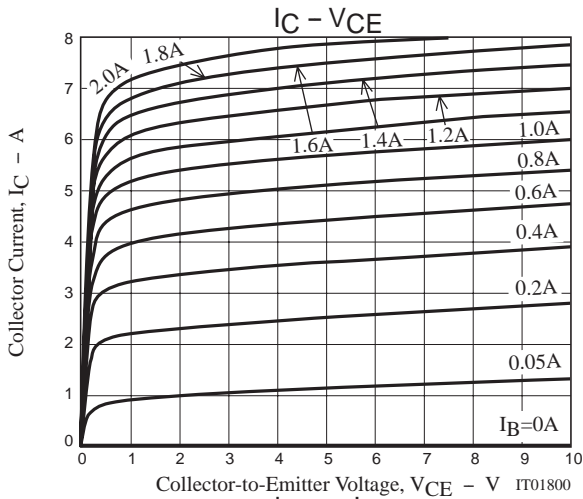
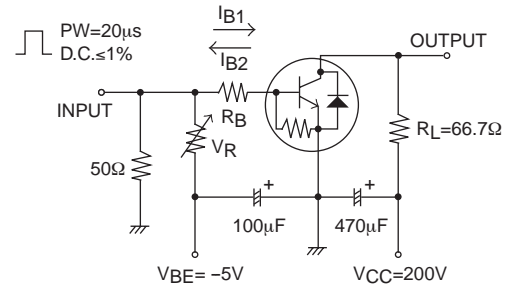
## Package Dimensions

unit : mm (typ)

7509-003



## Switching Time Test Circuit



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